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(22) 2003 03 05

(30) JP-P-2002-00059591 2002 03 05 (JP)

(71) 가 가 2 5 5

(72) 1-35-4

1-218-301

(74)

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(54) ,

(60) (10) EL
(20) (60) , (30) (12) , (10)
(16) (60) 가 (60) (20)
(60) (60) (10)
, (60)가 (16) 가

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2a , 2b , 2c .
3a , 3b .
4a , 4b , 4c .
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7 6 .
8a , 8b , 8c 가
9a , , 9c , 9b
10a , 10b , 10c
11 .

* *
10 : 12 :
14 : 16 :
30 : 42 :
50 :

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 , (, ' EL ') , 가 (, ' EL ' , ,
) , EL
 , EL .

1 (16) 가 (10) (12), (14),
(18) (16) , (18)
(18)가 (16) (18) (16) (28)
(28) (dark spot) 가 (28)
EL EL EL
가 가
1 1 2 1 1
2 가 가
1 2
가 가
가 가
1 1
2
가 가
2 1 1
2 1
가 가
2 1 1
2 1
가 가
2 1 1
2 1

EL 가

1

2

EL

1

1

2

EL 가

2 3 1 EL 2a (10)
(42) (12) (10) EL 가
(Thin Film Transistor: TFT)
(10) EL (10)
(Indium Tin Oxide: ITO)
a 1 (42) 1 (12) (12) EL
(12) (42)

2b (10) (30)
(10) (12)
(14) (42) (10) (30)
(30) (42) (10)
(30)가 (14) (10)

2c (16) (50) (30)
:NPB) , N, N' - di(- 1 - yl) - N, N' - (N, N' - Di(- 1yl) - N, N' -
(16)

3a (20) (60) (10)
(60) (30) (12) (20)
(60)가 EL (10) (16) (60)
(60) (20) (10)
(60)가 (16)가 (60)가

3b (22) (24) (22)
(50) (20)
(20) (22) 3a (20) (22)
(60) (20) (22) (22)
(24) (50) (20) (22) (22) (10)
EL

4a (30) (10) 3 x 3 (42) ,
 (50)가 (42) (10) (30)가 (30)가 (50)가 (42) (42)
 4
 4b (10) (10) (30) (30)가
 (42) (30) 3-5 μ m
 4c (30) (60) (42) 가
 (60)가 (60)
 5 (30) (30)가 (42)
 , (42) 4 5 (30)
 , 가 가
 6 (10) (42) (30) (42) (44) (14)
) (44) (30) (30) (42) (30) (10)
 , (30) (42)
 7 6 (30)
 (42) (30) (42) (30)
 , (20)
 , (42) (30) (30) (30)
 가 (16), (22) 가 (24) (30) (24) 가 (30)
 , (30)
 8 (10) (30) 8a
 , (10) (14) , 8b
 , (14) , 8c
 , 가 가 (30)
 (30) (30) (16) (30) (30)
 (30)가 (30) 가 (14) (30) 가
 (30) (14)
 9 2 EL 9a (10) (4
 2) (12), (14) (16)
 9b (20) (12) (80) (70)가
 (72) , (72) (14) (72) (10)
 (80) (16) (20) (70)
 (20) (12) (72)가 (10) (16)
 (72)가 (10)
 9c (20) (22) (24) (
 22) 9b (70) (20) (24)
 (50) (50) (80)

, 9b (70) 가 (80) .

10a (80) (74) (72) , 3 x 3 (74) (72) , (80) (10) , (70)가 (80) (10) , (80)가 (72)가 (74) (74) 4 (80) (72) (80) 가

10b (70) (72) (80) 가 (74) (72) .

10c (80) (10) (70) 9 b (80) (14) (10) 가 (72)가 , (70) .

11 (80) (74) 10 11 (80)가 (80) (74) 가 가

가 가

EL

가

(70) (10) 가

(57)

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11 12. ,

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14.

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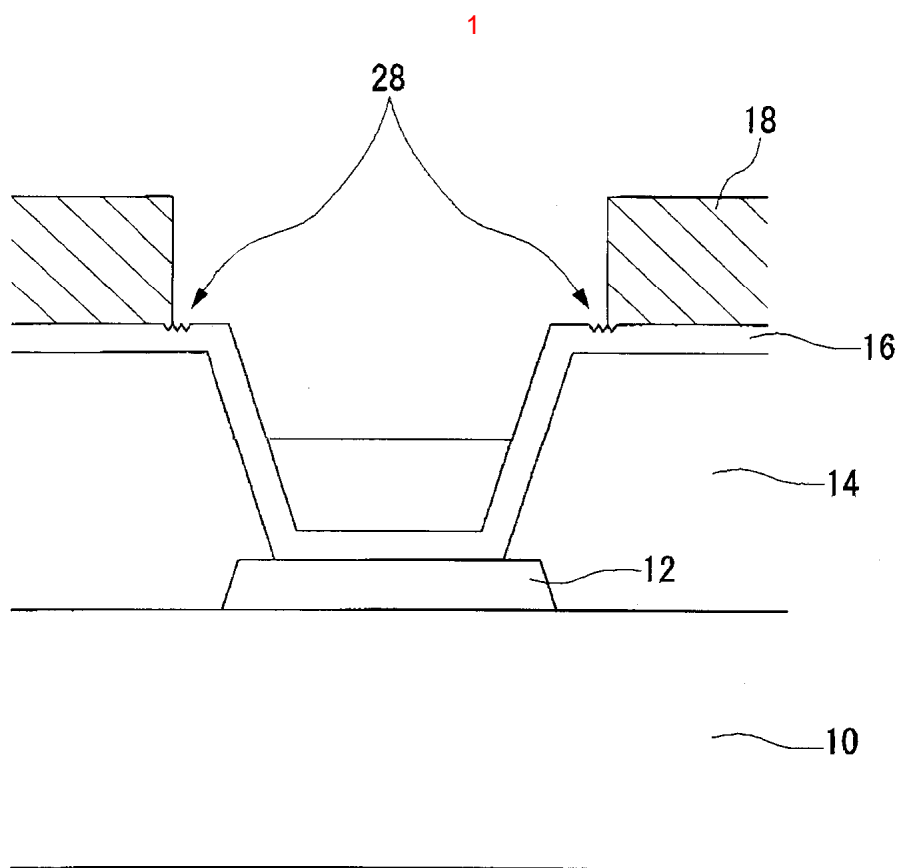
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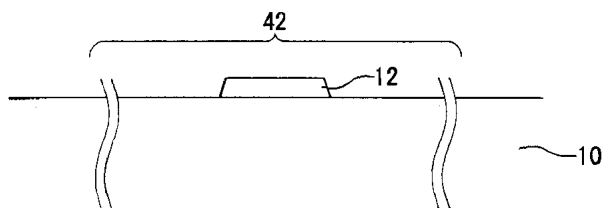
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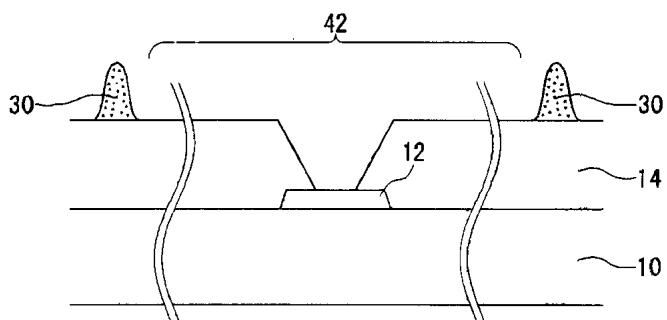


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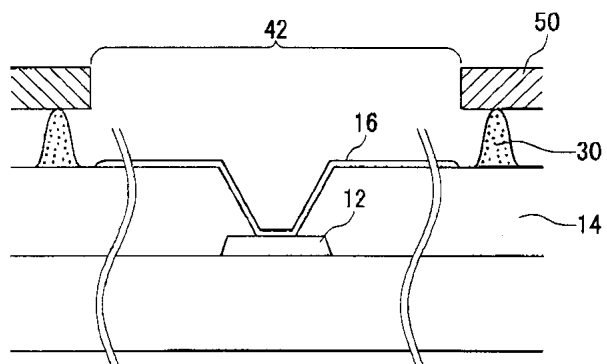
(a)



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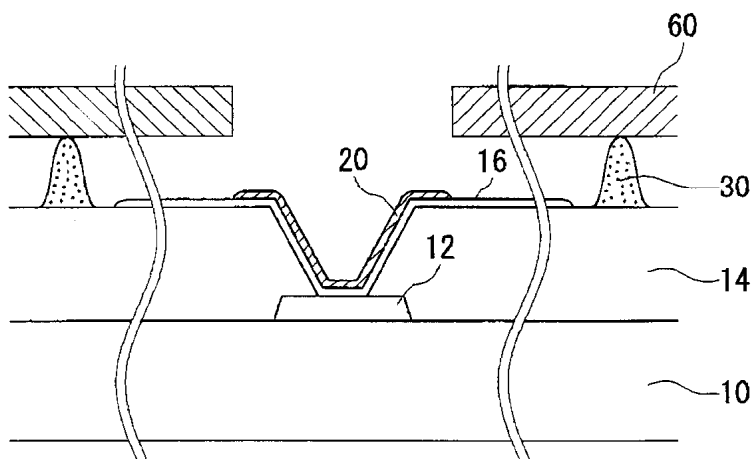


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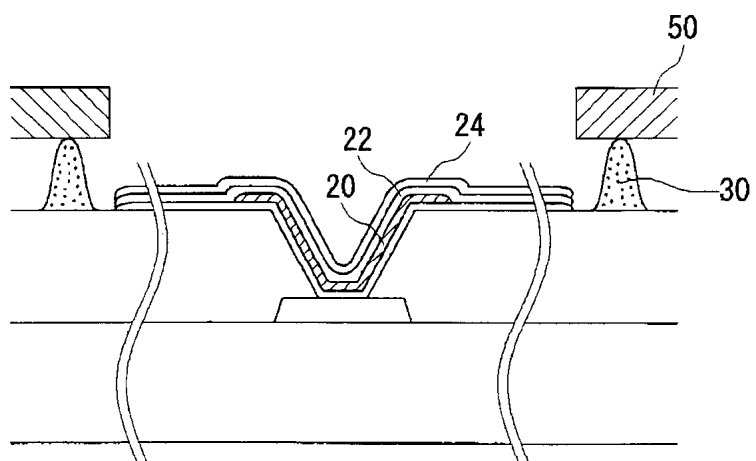


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(a)

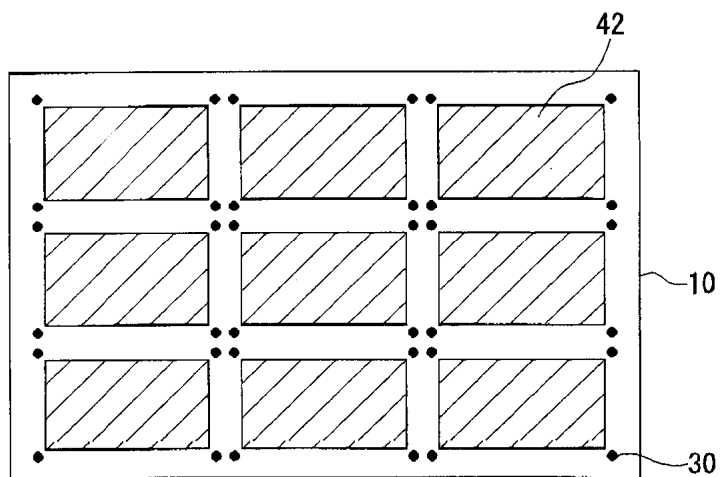


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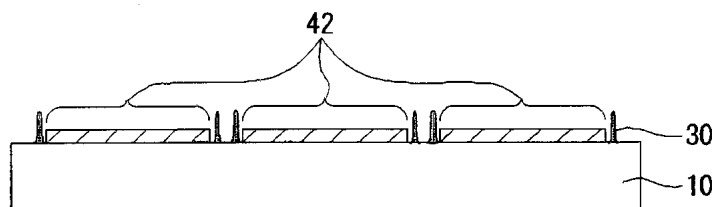


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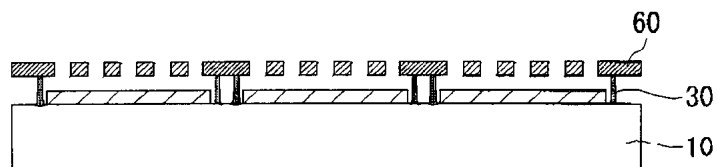
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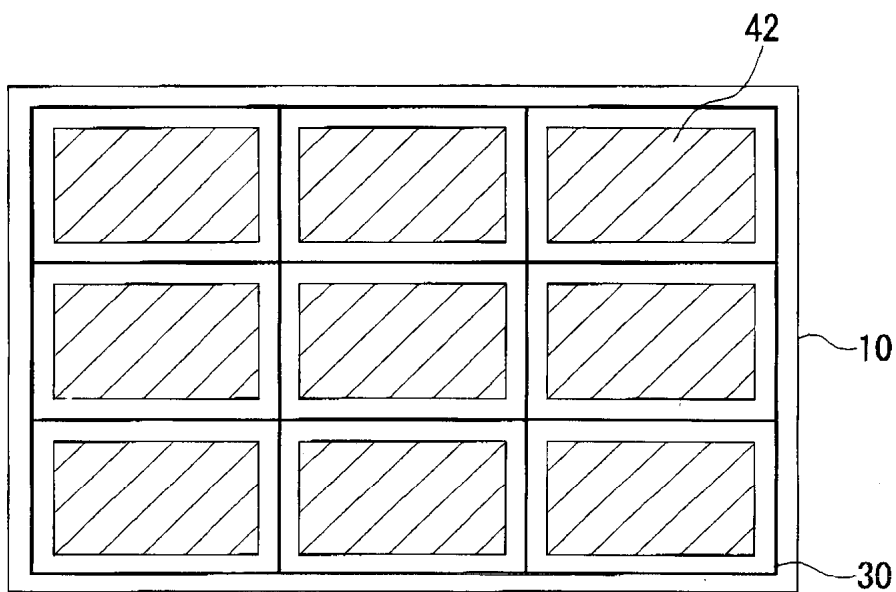
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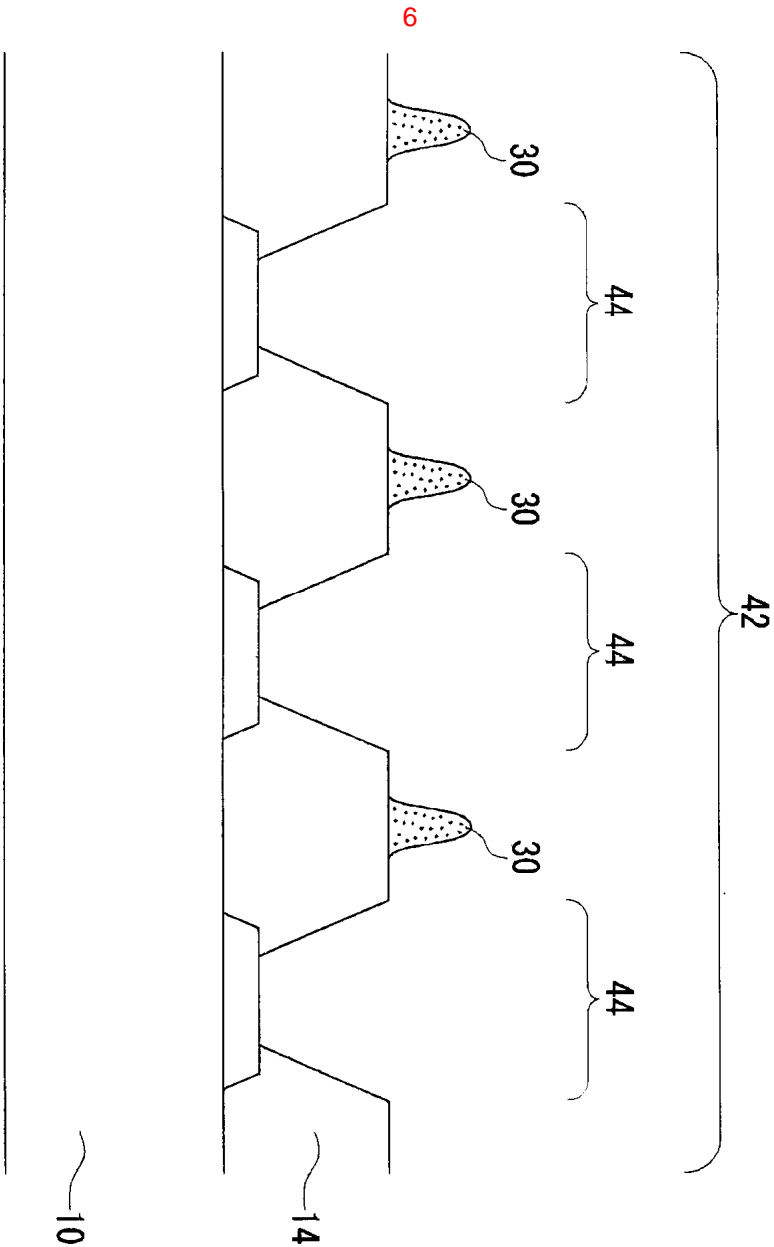


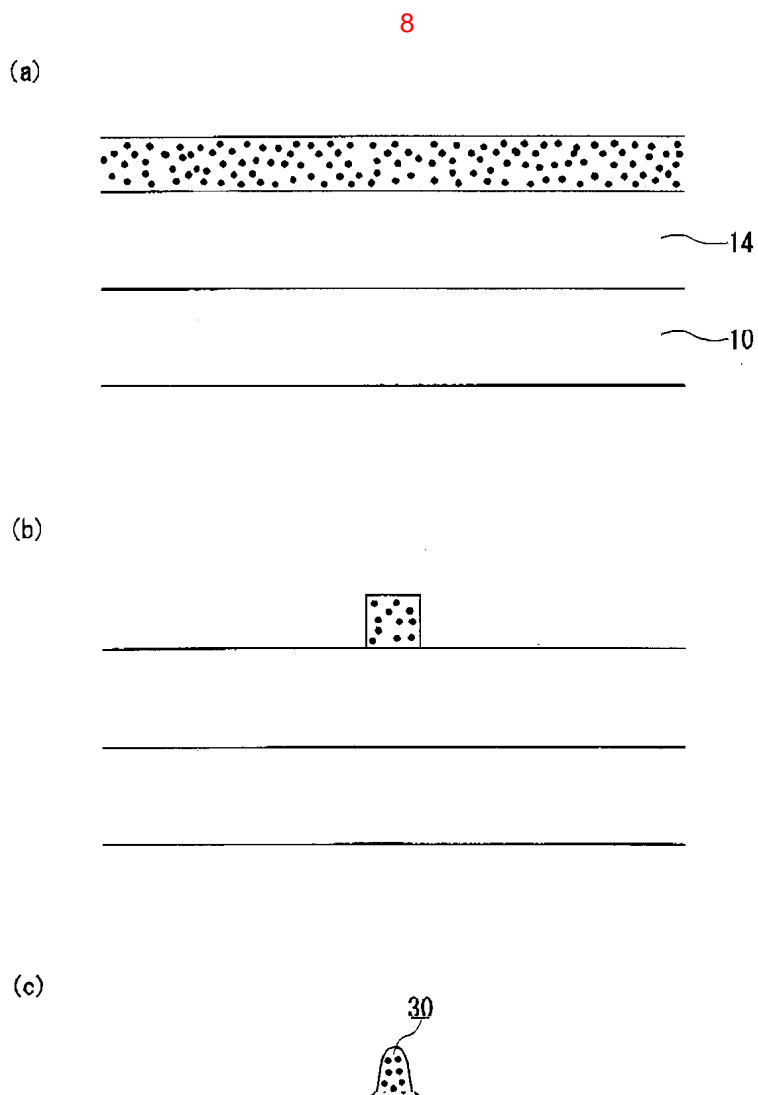
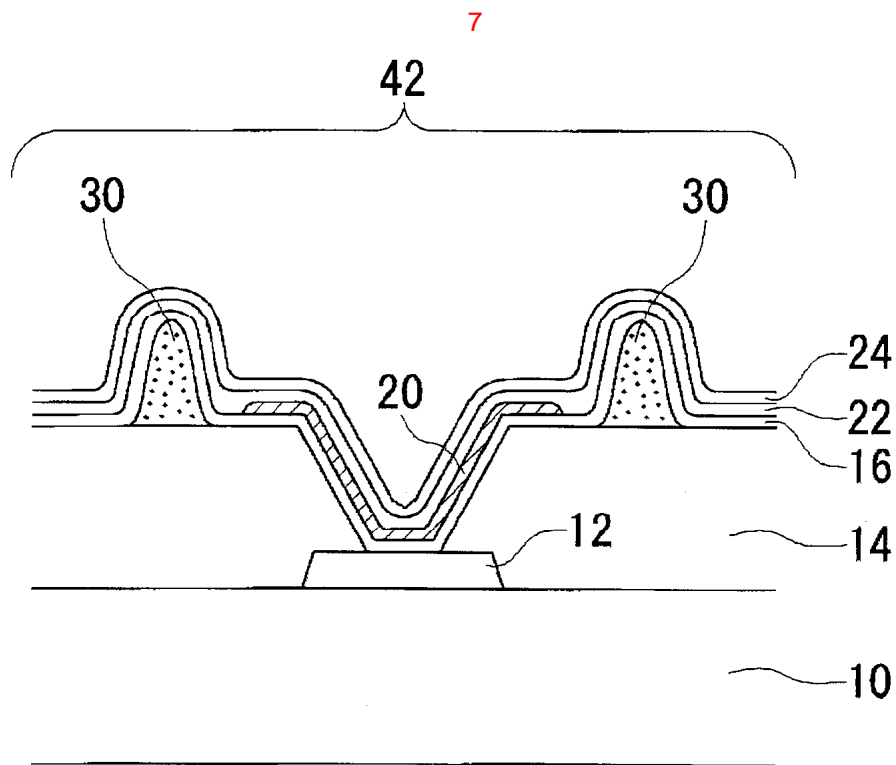
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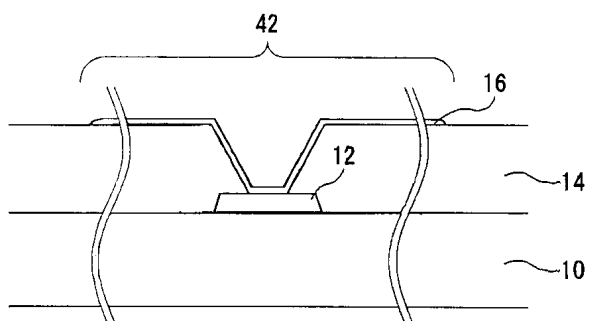




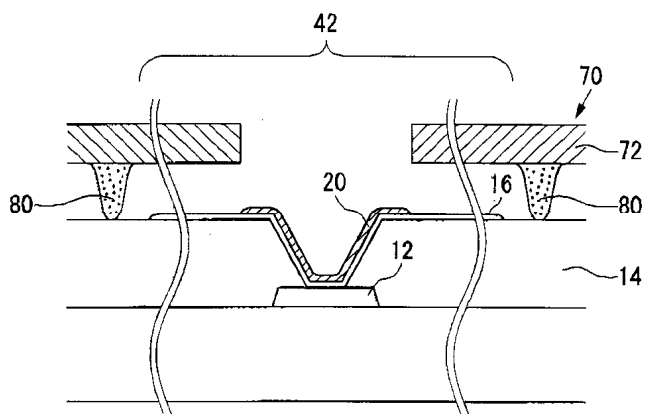


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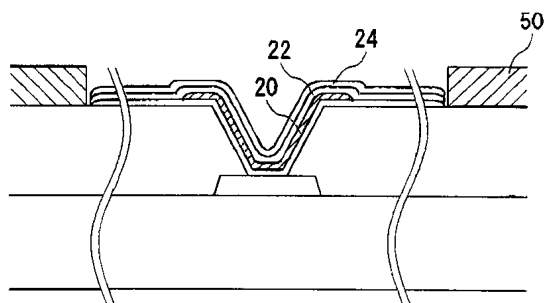
(a)



(b)

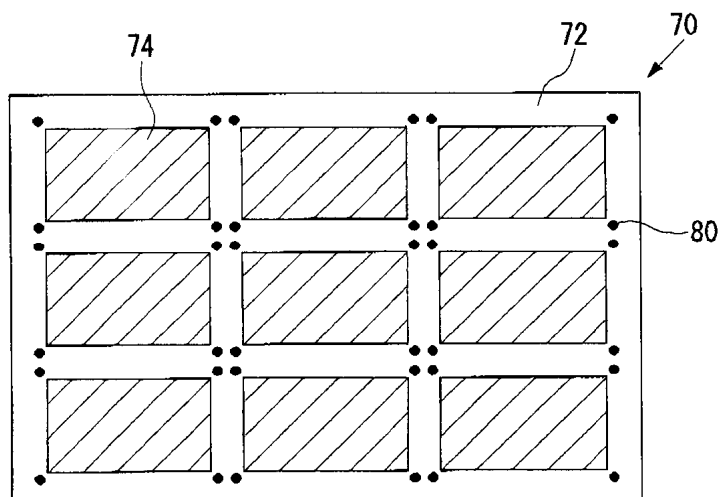


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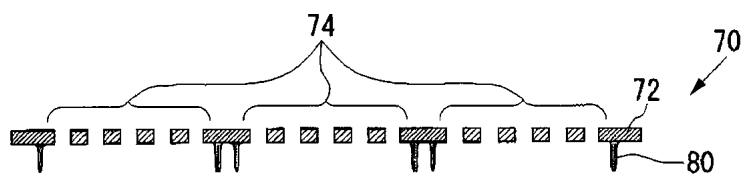


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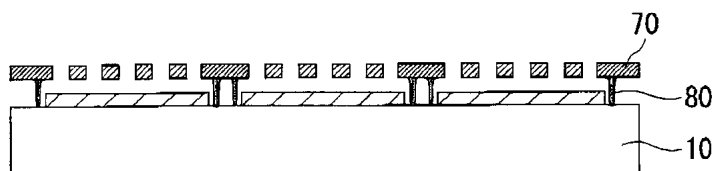
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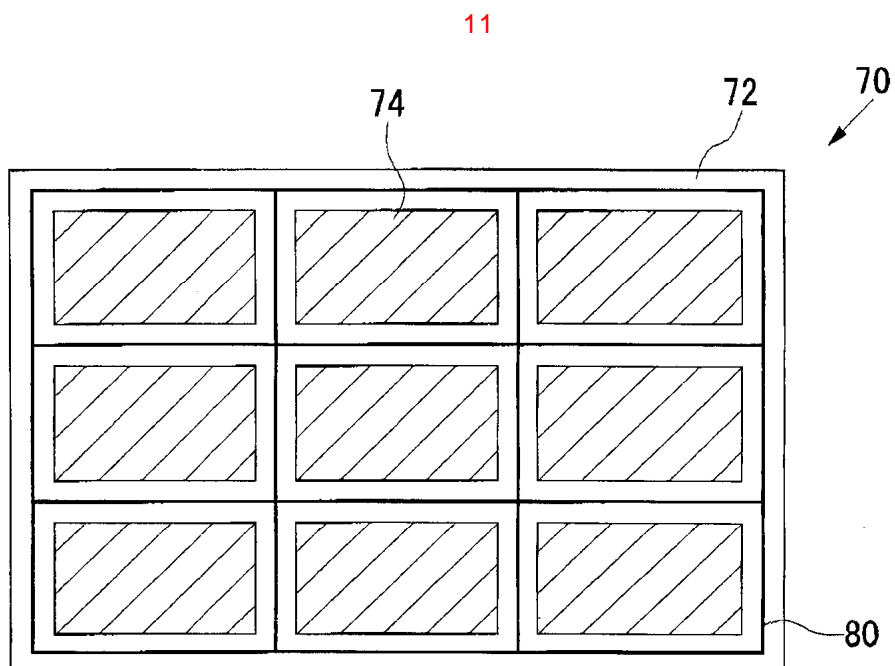


(b)



(c)





专利名称(译)	制造有机电致发光板，有机电致发光器件和掩模的方法		
公开(公告)号	KR1020030074227A	公开(公告)日	2003-09-19
申请号	KR1020030013684	申请日	2003-03-05
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当前申请(专利权)人(译)	三洋电机有限公司是分租		
[标]发明人	NISHIO YOSHITAKA 니시오요시따까 MATSUKI HIROSHI 마쓰끼히로시		
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IPC分类号	H01L51/40 H01L51/50 H05B33/10 H01L51/56 H05B33/12 H01L27/32 H01L51/00		
CPC分类号	H01L51/56 H01L51/0013 H01L51/001 H01L27/3295 H01L27/3211		
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优先权	2002059591 2002-03-05 JP		
外部链接	Espacenet		

摘要(译)

形成有机EL面板的制造方法，该有机EL面板形成有机发光层，存在于下层中的有机层不受损伤。它布置成将发光层沉积掩模（60）与基板（10）分开的状态。有机发光材料沉积在空穴注入阳极（12）的上侧，并形成有机发光层（20）。掩模（60）的下侧与隔离物（30）的上侧接触并排列。以这种方式，可以在空间上将掩模（60）与基板（10）上的空穴传输层（16）分离。在有机发光层（20）的着色层连续蒸发过程中，必须具有掩模（60）的精细位置对准。然而，对将掩模（60）与基板（10）分开的状态进行位置对准。以这种方式，可以减少掩模（60）损伤空穴传输层（16）的可能性。有机发光二极管，空穴传输层，掩模，间隔物。

